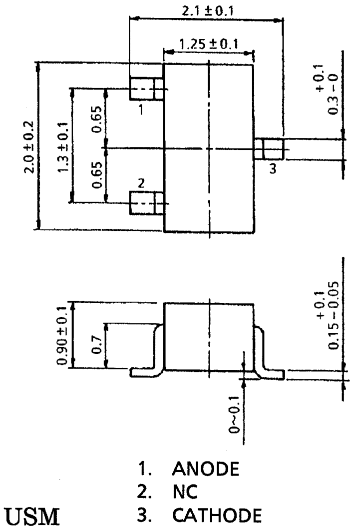
TOSHIBA Diode Silicon Epitaxial Shottky Barrier Type

1SS401

High Speed Switching Applications

- Low forward voltage : $V_{F(3)}$ = 0.38 V (typ.)
- Low reverse current : I_R = 50μA (max)
- Small total capacitance : C_T = 46 pF (typ.)

Unit in mm



JEDEC	—
JEITA	SC-70
TOSHIBA	1-2P1D

Weigh: 0.006 g(typ.)

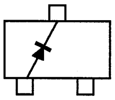
Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	25	V
Reverse voltage	V_R	20	V
Maximum (peak) forward current	I_{FM}	700	mA
Average forward current	I_O	300	mA
Power dissipation	P	100	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C
Operating temperature range	T_{opr}	−40~100	°C

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_{F(1)}$	—	I_F = 1mA	—	0.16	—	V
	$V_{F(2)}$	—	I_F = 10mA	—	0.22	—	
	$V_{F(3)}$	—	I_F = 300mA	—	0.38	0.45	
Reverse current	I_R	—	V_R = 20V	—	—	50	μA
Total capacitance	C_T	—	V_R = 0, f = 1MHz	—	46	—	pF

Pin Assignment (Top View)



Marking